

# PBSS5240Z 40 V, 2 A PNP low VCEsat (BISS) transistor 15 October 2014

**Product data sheet** 

#### **General description** 1.

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4240Z

#### 2. **Features and benefits**

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

## **Applications**

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

#### Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-40	V
Ic	collector current		-	-	-2	Α
I <sub>CM</sub>	peak collector current	$t_p \le 1$ ms; single pulse	-	-	-3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	320	mΩ



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# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	Е	emitter		. M
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym028

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS5240Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5240Z	S5240Z

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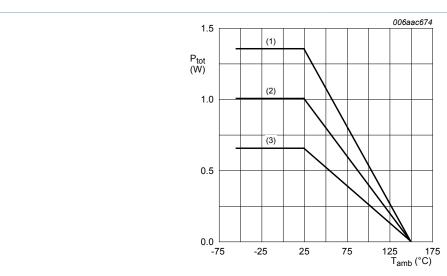
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-40	V
$V_{CEO}$	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-2	Α
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	-3	Α
I <sub>B</sub>	base current			-	-300	mA
I <sub>BM</sub>	peak base current	t <sub>p</sub> ≤ 1 ms; single pulse		-	-1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

PBSS5240Z

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#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
and a)	thermal resistance	in free air	[1]	-	-	192	K/W
	from junction to ambient		[2]	-	-	125	K/W
	ambient		[3]	-	-	93	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

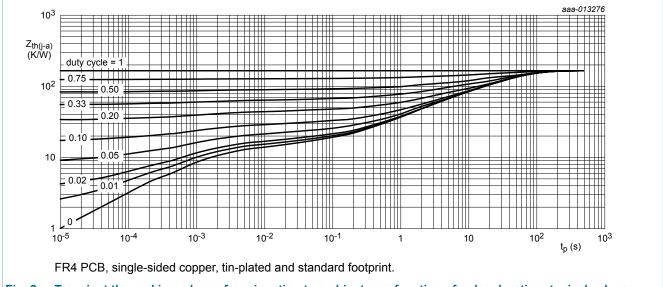
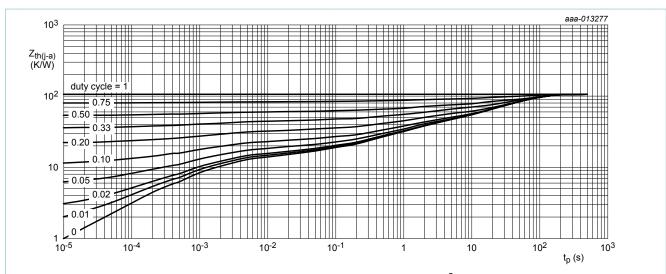


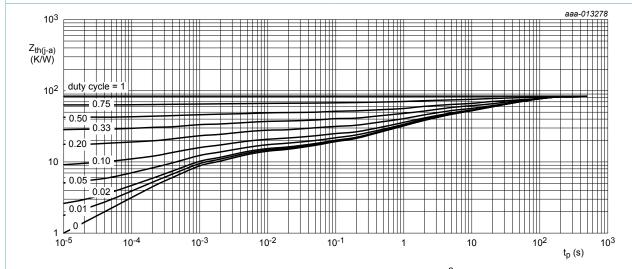
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

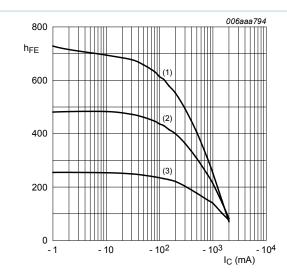
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# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -32 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -32 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
Ices	collector-emitter cut-off current	$V_{CE} = -32 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
ЕВО	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -1 mA; $T_{amb}$ = 25 °C	300	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -500 mA; $t_{p}$ ≤ 300 μs; $\bar{o}$ ≤ 0.02; $T_{amb}$ = 25 °C	215	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -1 A; $t_{p}$ ≤ 300 $\mu$ s; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	145	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -2 A; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	55	-	-	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = -100 mA; $I_B$ = -1 mA; $T_{amb}$ = 25 °C	-	-	-140	mV
	saturation voltage	$I_C$ = -500 A; $I_B$ = -50 mA; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-170	mV
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300  \mu\text{s}; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	-320	mV
		$I_{C}$ = -2 A; $I_{B}$ = -200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	-650	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	320	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -5 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	-1.1	V
fτ	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	150	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	12	pF

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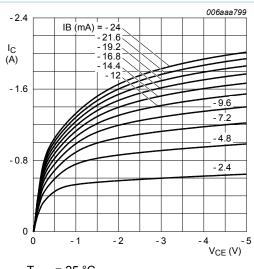
$$V_{CE}$$
 = -5  $V$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

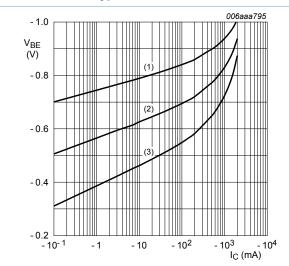
(3) 
$$T_{amb} = -55$$
 °C

Fig. 5. DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



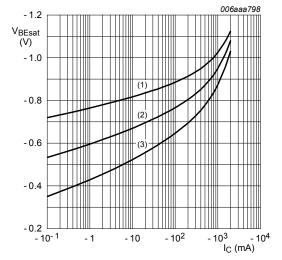
$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = 100 °C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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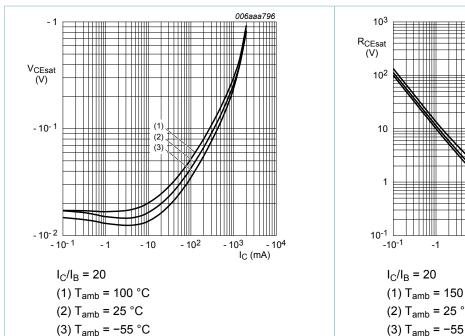


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

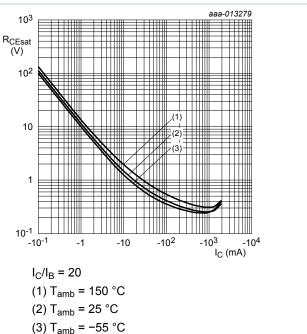


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

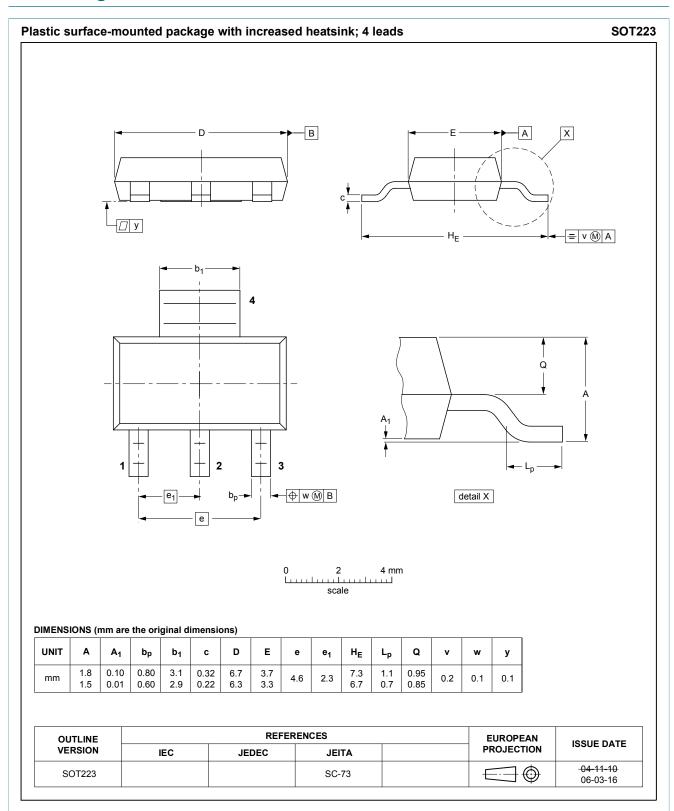
#### 11. Test information

#### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

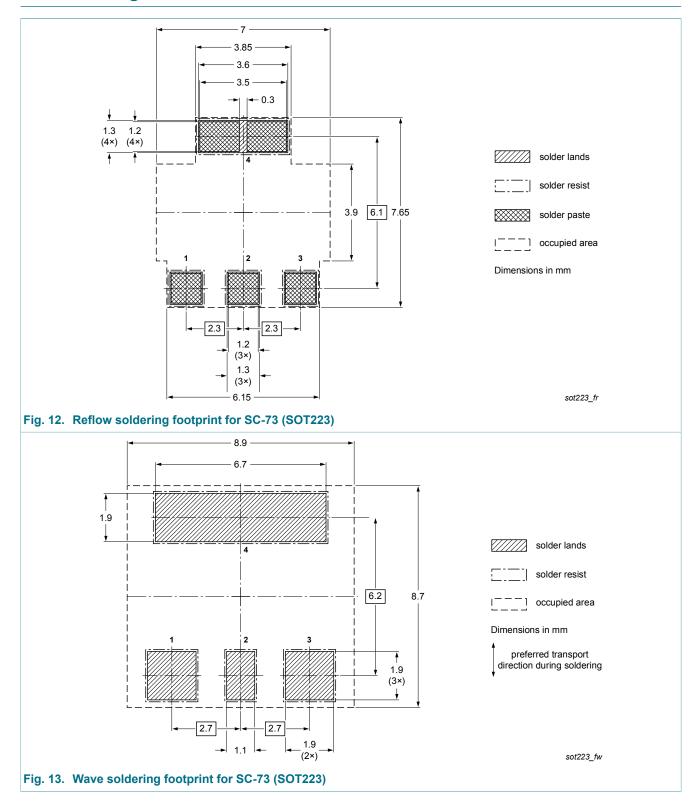
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# 12. Package outline



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# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5240Z v.1	20141015	Product data sheet	-	-

#### 40 V, 2 A PNP low VCEsat (BISS) transistor

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